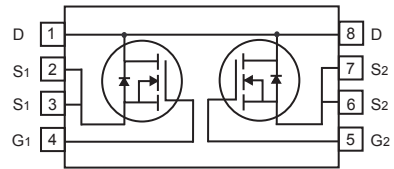
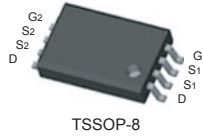


Dual N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 20V, 6A, $R_{DS(ON)} = 25m\Omega$ @ $V_{GS} = 4.5V$.
 $R_{DS(ON)} = 35m\Omega$ @ $V_{GS} = 2.5V$.
- Super High dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TSSOP-8 for Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	6	A
Drain Current-Pulsed ^a	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.5	W
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient ^b	$R_{\theta JA}$	83	$^\circ C/W$



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Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 18V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 12V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -12V, V_{DS} = 0V$			-100	nA
On Characteristics ^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	0.5		1.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 4.5A$		21	25	$m\Omega$
		$V_{GS} = 2.5V, I_D = 3.5A$		27	35	$m\Omega$
Dynamic Characteristics ^d						
Input Capacitance	C_{iss}	$V_{DS} = 8V, V_{GS} = 0V, \square$ $f = 1.0\text{ MHz}$		720		pF
Output Capacitance	C_{oss}			130		pF
Reverse Transfer Capacitance	C_{rss}			95		pF
Switching Characteristics ^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 1A,$ $V_{GS} = 4.5V, R_{GEN} = 6\Omega$		10	20	ns
Turn-On Rise Time	t_r			7	14	ns
Turn-Off Delay Time	$t_{d(off)}$			34	68	ns
Turn-Off Fall Time	t_f			6	12	ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$		6.8	8.8	nC
Gate-Source Charge	Q_{gs}			0.5		nC
Gate-Drain Charge	Q_{gd}			1.8		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				1.7	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 1.7A$			1.2	V
Notes : \square a.Repetitive Rating : Pulse width limited by maximum junction temperature. \square b.Surface Mounted on FR4 Board, $t \leq 10\text{ sec.}$ \square c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. \square d.Guaranteed by design, not subject to production testing. \square \square						



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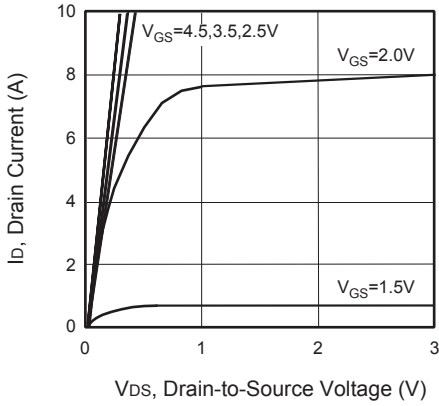


Figure 1. Output Characteristics

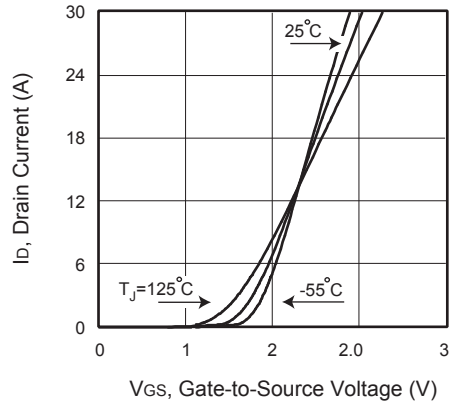


Figure 2. Transfer Characteristics

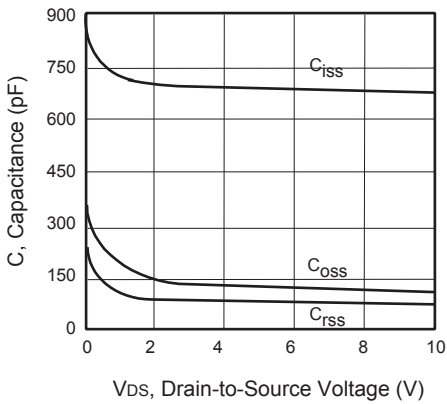


Figure 3. Capacitance

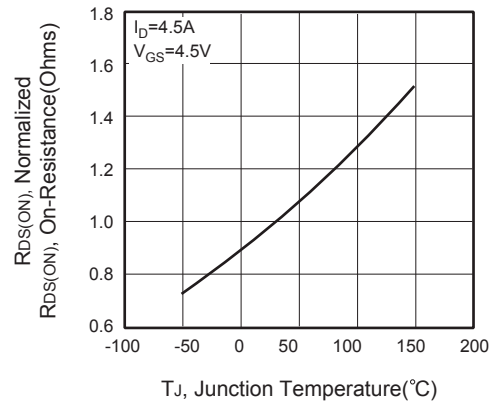


Figure 4. On-Resistance Variation with Temperature



Figure 5. Gate Threshold Variation with Temperature

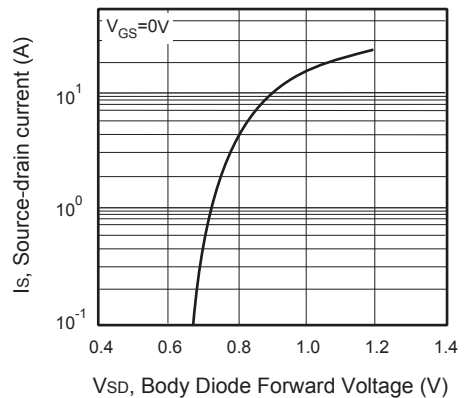


Figure 6. Body Diode Forward Voltage Variation with Source Current



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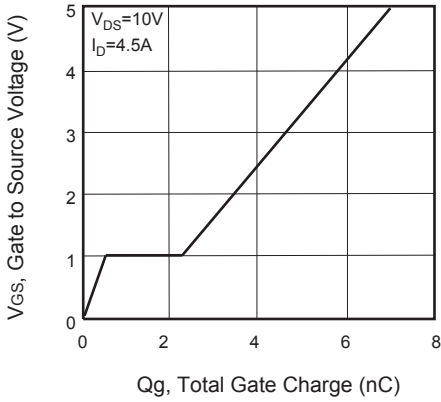


Figure 7. Gate Charge

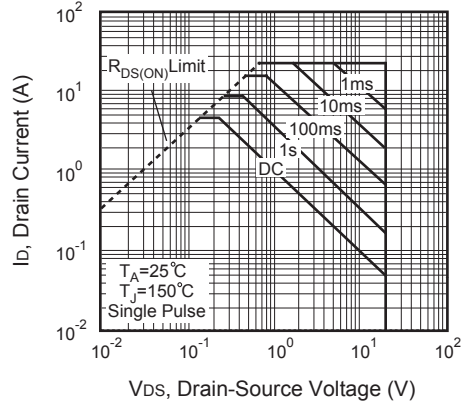


Figure 8. Maximum Safe Operating Area



Figure 9. Switching Test Circuit



Figure 10. Switching Waveforms

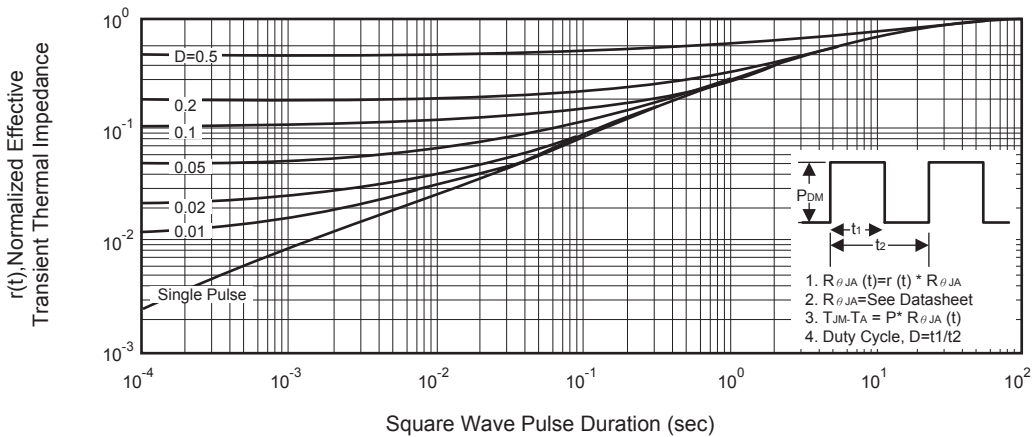


Figure 11. Normalized Thermal Transient Impedance Curve